MAY 13 2005
PATENT & TRADEMARK OFFICE

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:	Charles Dennison	§	
		§	
		§	Art Unit: 2822
Serial No.:	10/679,637	§	
		§	Examiner: Kevin M. Picardat
Filed:	October 6, 2003	§	
		§	Docket: ITO.0532D1US P10295D
For:	Method to Selectively Increase the Top Resistance of the Lower Programming Electrode in a Phase-Change Memory Cell and Structures Obtained Thereby	§	
		§	Assignee: Intel Corporation

Mail Stop **Amendment**
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO PAPER NO. 20050303

Sir:

In response to the office action mailed March 9, 2005, please amend the above-referenced patent application as follows:

Date of Deposit: May 11, 2005
I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Cynthia L. Hayden